

INCHANGE SEMICONDUCTOR

isc P-Channel MOSFET Transistor

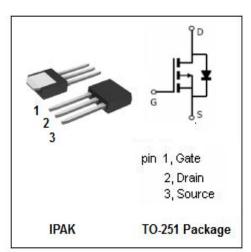
IRFU9024N

·FEATURES

- Static drain-source on-resistance:
 - RDS(on)≤175mΩ(@V_{GS}= -10V; I_D= -6.6A)
- Advanced trench process technology
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

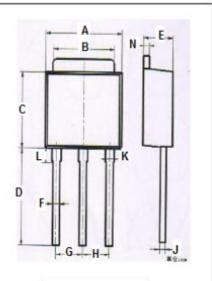
APPLICATIONS

• Fast switching application.



• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT				
V _{DSS}	Drain-Source Voltage	-55	V				
V_{GS}	Gate-Source Voltage	±20	V				
ID	Drain Current-Continuous	-11	А				
PD	Total Dissipation @Tc=25°C	28	W				
Tj	Max. Operating Junction Temperature	-55~150	°C				
T _{stg}	Storage Temperature	-55~150	°C				
• THERMAL CHARACTERISTICS							
SYMBOL	PARAMETER	МАХ	UNIT				



	mm	
DIM	MIN	MAX
Α	6.40	6.48
В	5.10	5.50
С	5.80	6.20
D	9.20	9.60
Ε	2.20	2.40
F	0.50	0.70
G	2.09	2.49
Н	2.09	2.49
J	0.40	0.60
Κ	0.70	0.90
L	1.60	2.00
Ν	0.40	0.60

Channel-to-case thermal resistance

Rth(j-c)

°C/W

3.3

1



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ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = -250uA	-55		V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} ; I _D = -1.7mA	-2	-4	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = -10V; I _D = -6.6A		175	mΩ
Igss	Gate-Source Leakage Current	V _{GS} = ±20V; V _{DS} = 0V		±100	nA
IDSS	Drain-Source Leakage Current	V _{DS} = -55V; V _{GS} = 0V		-25	μA
V _{SD}	Diode forward voltage	I _S = -7.2A, V _{GS} = 0V		-1.6	V

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